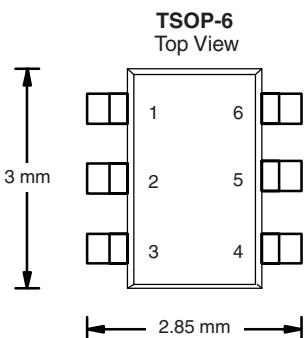


P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 20	0.027 at V _{GS} = - 4.5 V	- 7	21
	0.035 at V _{GS} = - 2.5 V	- 6.2	
	0.048 at V _{GS} = - 1.8 V	- 5.2	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET: 1.8 V Rated
- Ultra-Low On-Resistance
- Compliant to RoHS Directive 2002/95/EC

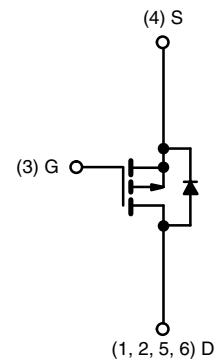


Ordering Information: Si3493DV-T1-E3 (Lead (Pb)-free)
Si3493DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: 93xxx

APPLICATIONS

- Load Switch
- PA Switch
- Battery Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 20		V	
Gate-Source Voltage	V _{GS}		± 8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 7	A	
	T _A = 85 °C		- 3.6		
Pulsed Drain Current	I _{DM}	- 20			
Continuous Source Current (Diode Conduction) ^a	I _S	- 1.7	- 0.9		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0	W	
	T _A = 85 °C		1.0		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	45	°C/W
	Steady State		90	
Maximum Junction-to-Foot (Drain)	R _{thJF}	25	30	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	- 0.40		- 1	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μA
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^\circ\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$		0.022	0.027	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$		0.029	0.035	
		$V_{GS} = -1.8 \text{ V}, I_D = -3 \text{ A}$		0.039	0.048	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5 \text{ V}, I_D = -7 \text{ A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.7	- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$		21	32	nC
Gate-Source Charge	Q_{gs}			2.6		
Gate-Drain Charge	Q_{gd}			6		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \approx -1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 6 \Omega$		20	30	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(\text{off})}$			125	190	
Fall Time	t_f			85	130	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.7 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		64	90	

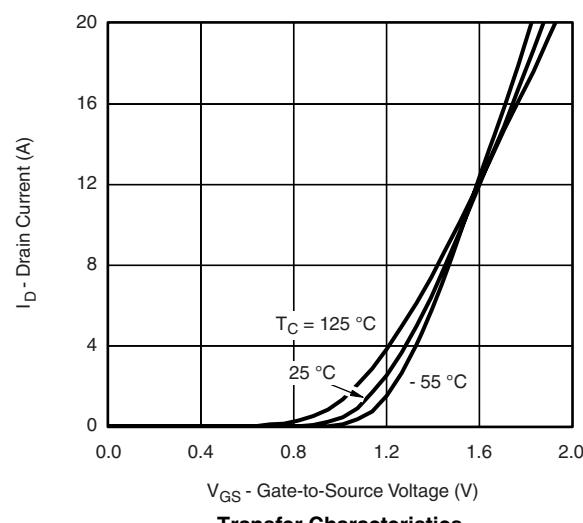
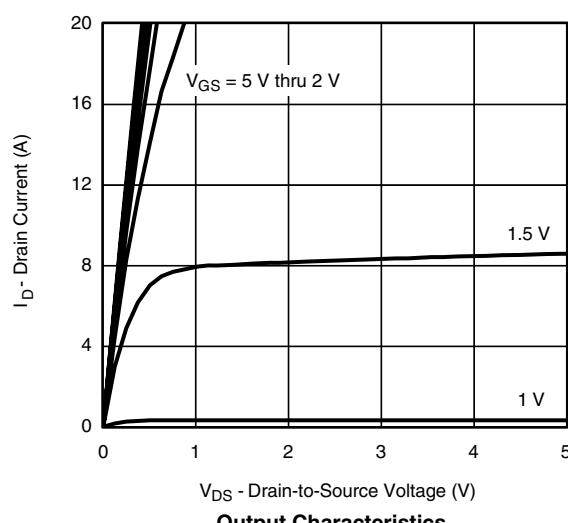
Notes:

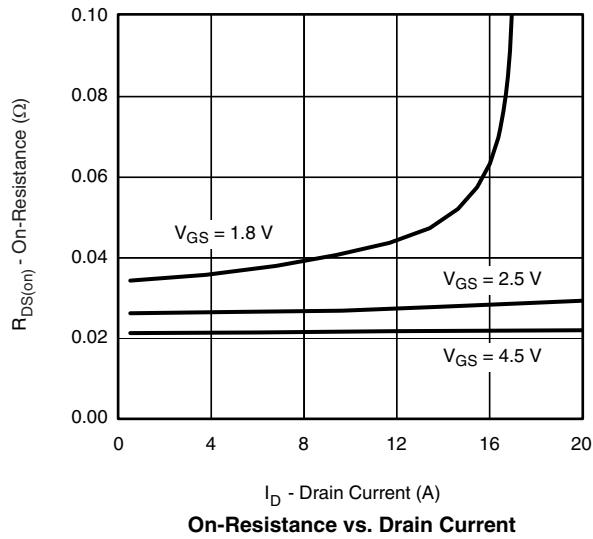
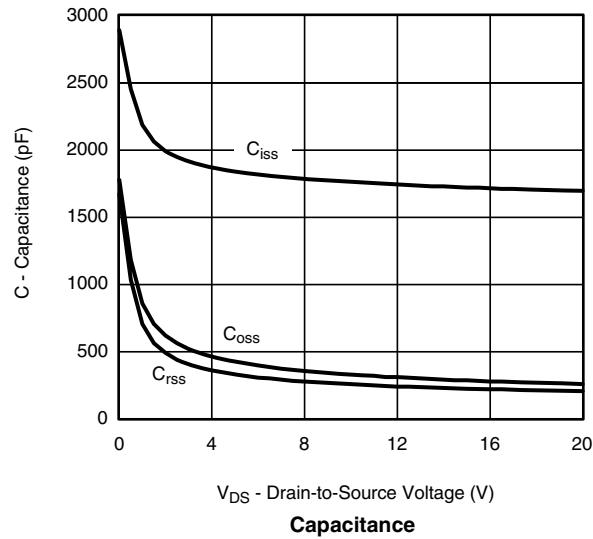
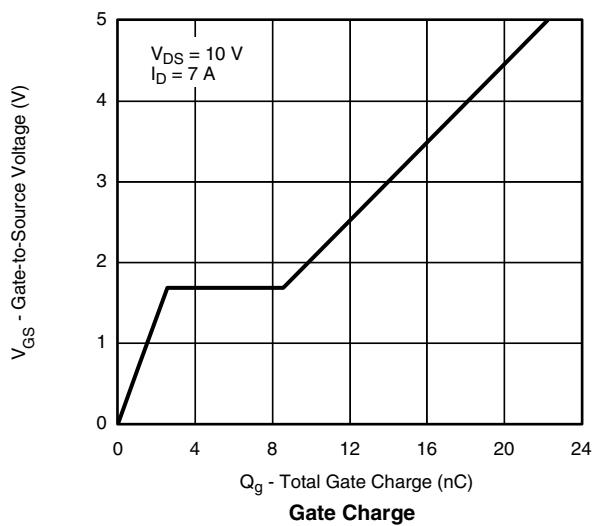
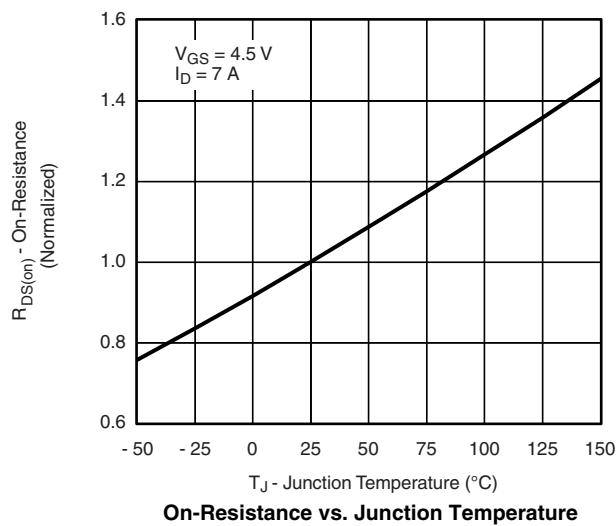
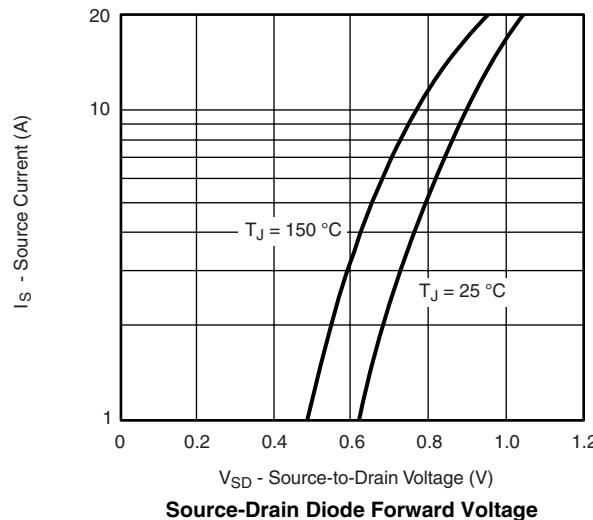
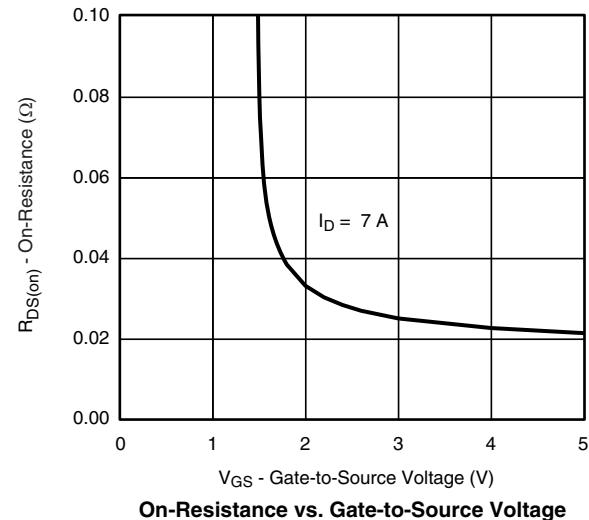
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.

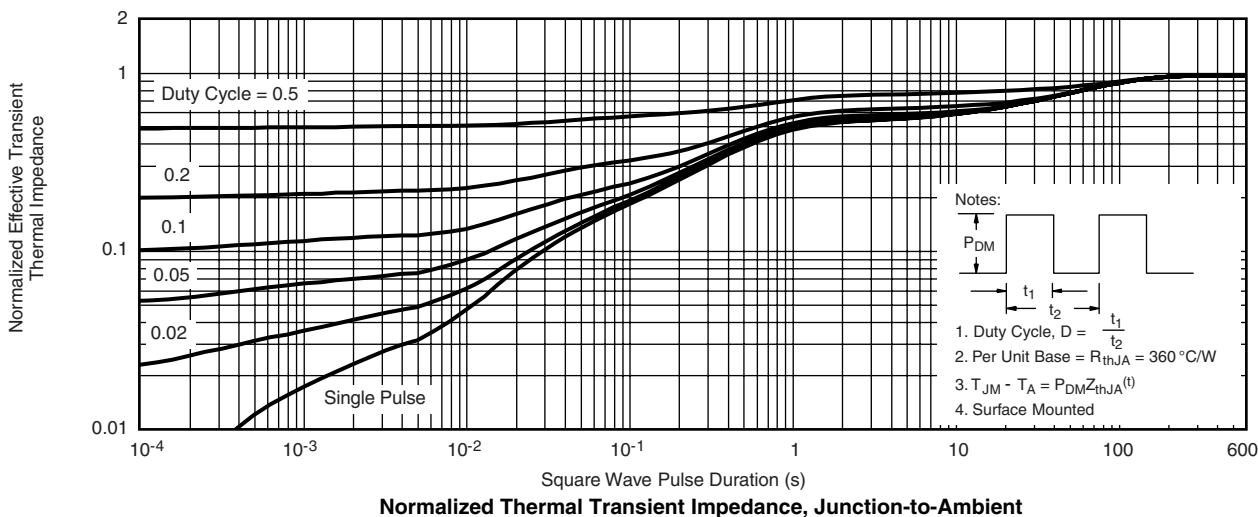
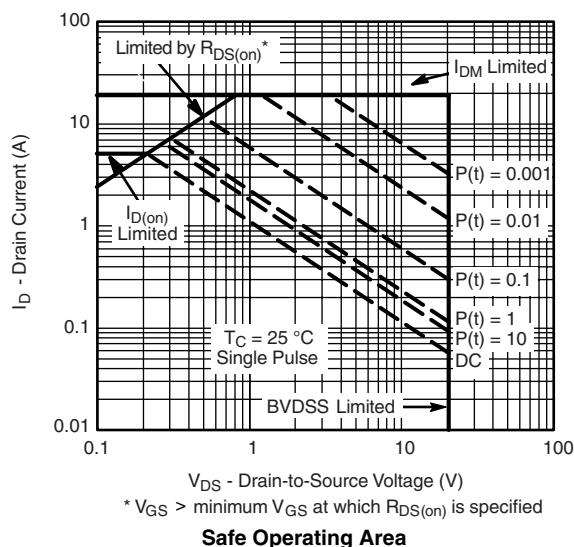
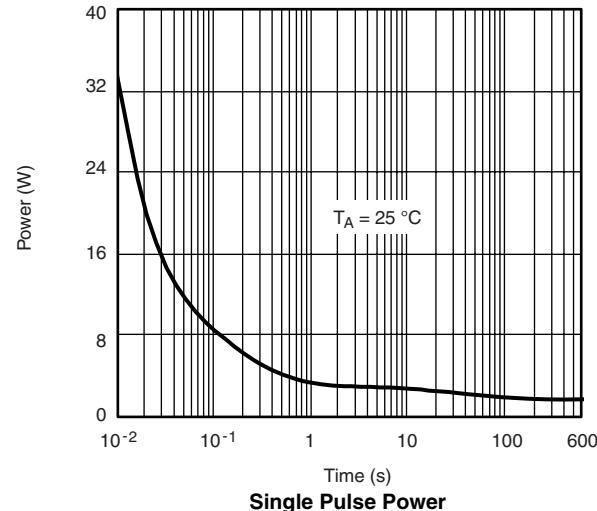
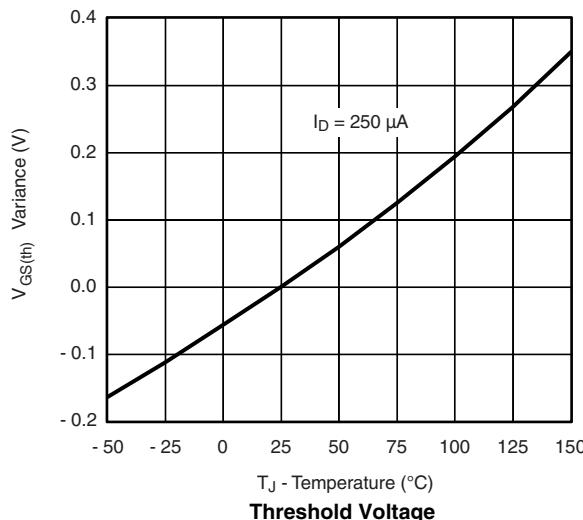
b. Guaranteed by design, not subject to production testing.

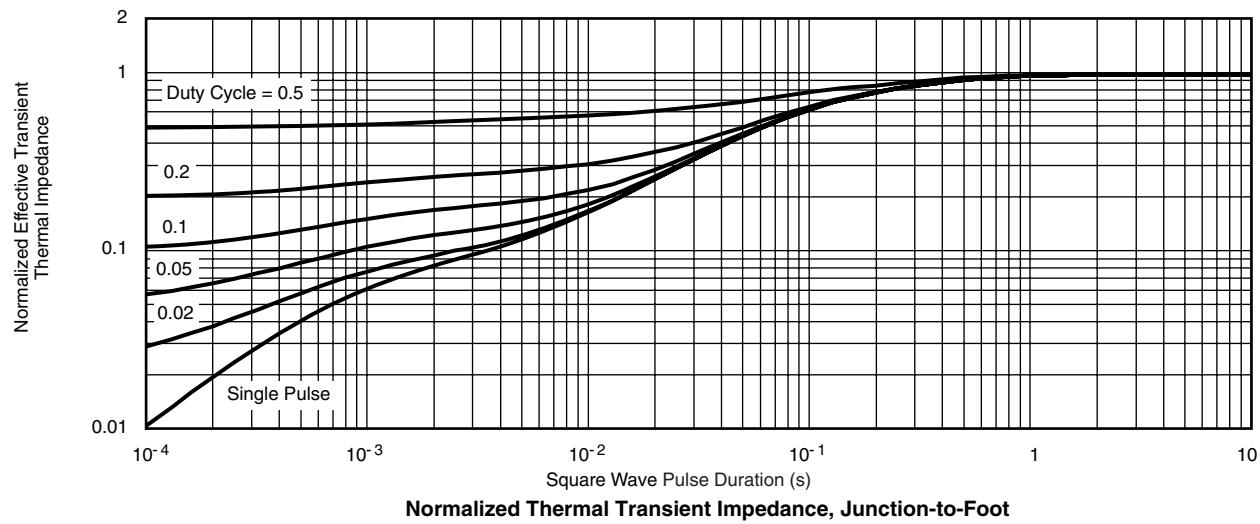
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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